

# QUART&T BO

27/01/2025

G. Bruni

- Quick general review of the project (widely using A. Giachero's slides)
- Groups and budget
- Working packages
- Kick-off meeting: proposed dates
- Local information

# QUART&T: Goal

A.G.

The QUantum Architectures for Theory & Technology (QUART&T) project aims to develop demonstrator quantum architectures, establishing the foundation for experimental platforms where theoretical models and phenomena of interest to the INFN can be tested.

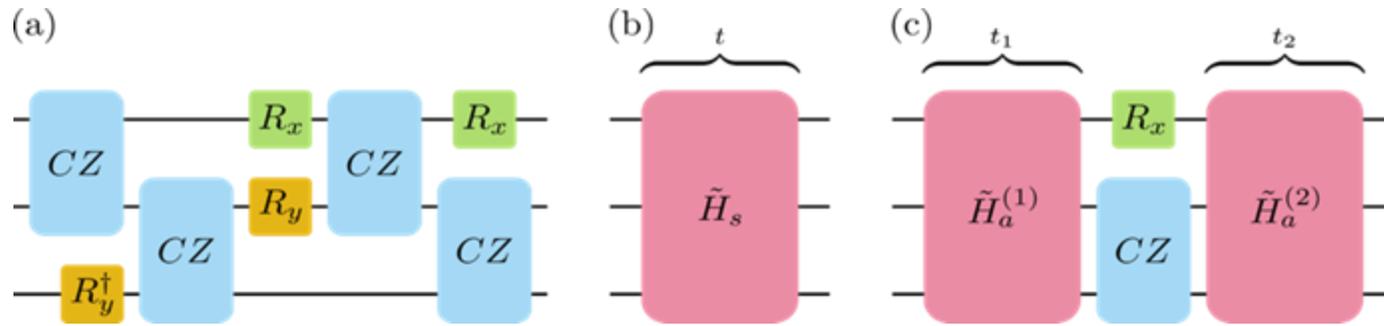
A **quartet** of crucial optimizations:

1. All-to-all connectivity;
2. Tunable couplings;
3. Higher-dimensional systems (Qudits);
4. Circuit Quantum Electrodynamics



The **project goal** and the **crucial optimizations** will be reached through:

1. Simulation and Design of quantum systems in 2D and 3D technologies;
2. Fabrication of circuits with S.C. resonators and qubits;
3. Software and hardware for qubit characterization, measurement, control and readout;
4. Theories and algorithms for quantum simulation, sensing and machine learning.



[Advances in Physics: X 3\(1\), 1457981 \(2018\)](#)

**(a) Digital simulation:**

$$H_s = H_1 + H_2 + \dots + H_n \Rightarrow U(t) = e^{-H_1 t/r} \cdot e^{-H_2 t/r} \cdot \dots \cdot e^{-H_n t/r}$$

Trotter–Suzuki decompositions: digital sequence tries to reproduce a targeted quantum evolution

**(b) Analog simulation:**

$$H_s = \tilde{H}_s \Rightarrow U(t) = T \int_0^t dt' H_0 + H_p(t') \leftarrow \text{Controllable pulse drive}$$

Controllable system with evolution  $H_s$  mimics almost one-to-one that of the simulated system  $H_s$

**(c) Digital Analog Simulation:**

$$H_s = \tilde{H}_a^{(1)} + H_1 + \dots + H_n + \tilde{H}_a^{(2)} \Rightarrow U(t) = \prod \tilde{H}_a^{(i)} \cdot H_j$$

Combines analog blocks that naturally appear in the simulator with digital gates

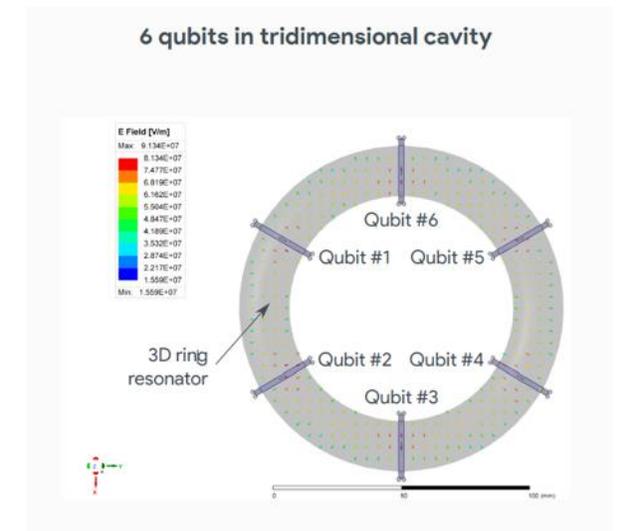
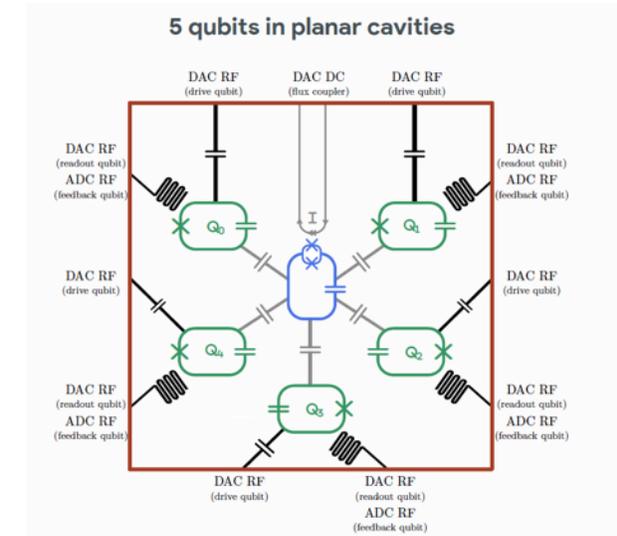
# Examples of quantum simulations of interest

- **Nuclear reactions and dynamics** - [Phys. Rev. A 108, 032417 \(2023\)](#)
  - neutrino-scattering in SN explosion and neutron star cooling
  - cross sections for dark-matter searches and neutrino physics
- **Lattice Quantum Chromo Dynamics (QCD)** - [Phys. Rev. Res. 5, 033184 \(2023\)](#)
- **Circuit Quantum Electrodynamics** – [Nat. Comm. 14, 3263 \(2023\)](#)
  - Simulation of relativistic QM, Dirac equation

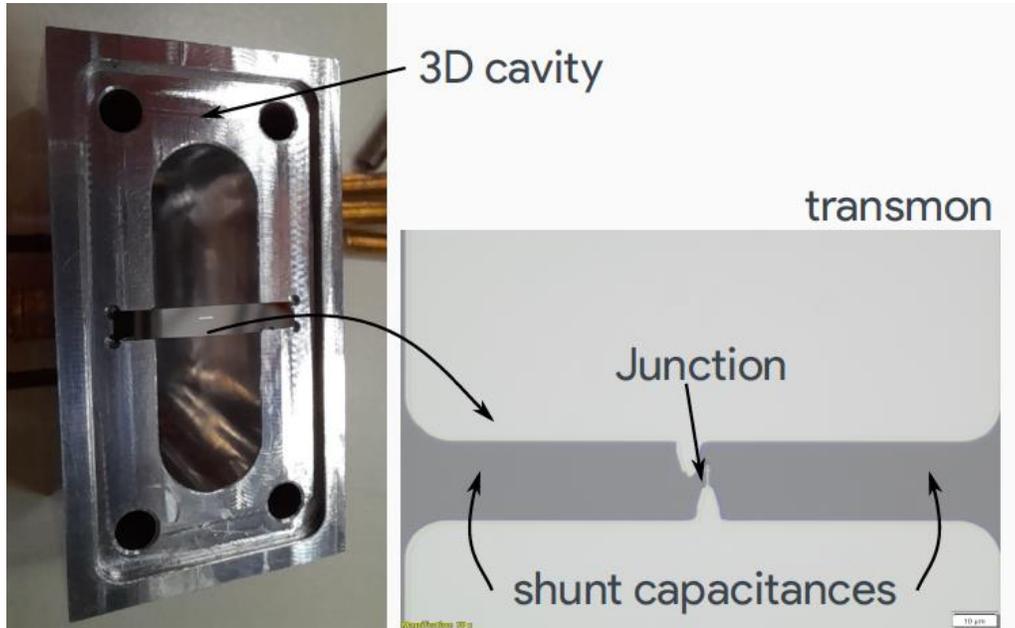
# The essential parts

1. Tunable couplings
2. All-to-all connectivity
  - Qubits coupled to a common bus resonator allow all-to-all coupling
  - Entanglement via tuning near common resonances
3. Qubits  $\rightarrow$  Qudits
4. cQED

[npj Quantum Inf 9, 40 \(2023\)](#)  
[Phys. Rev. X 11, 021058 \(2021\)](#)  
[arXiv:2405.00873 \[quant-ph\]](#)

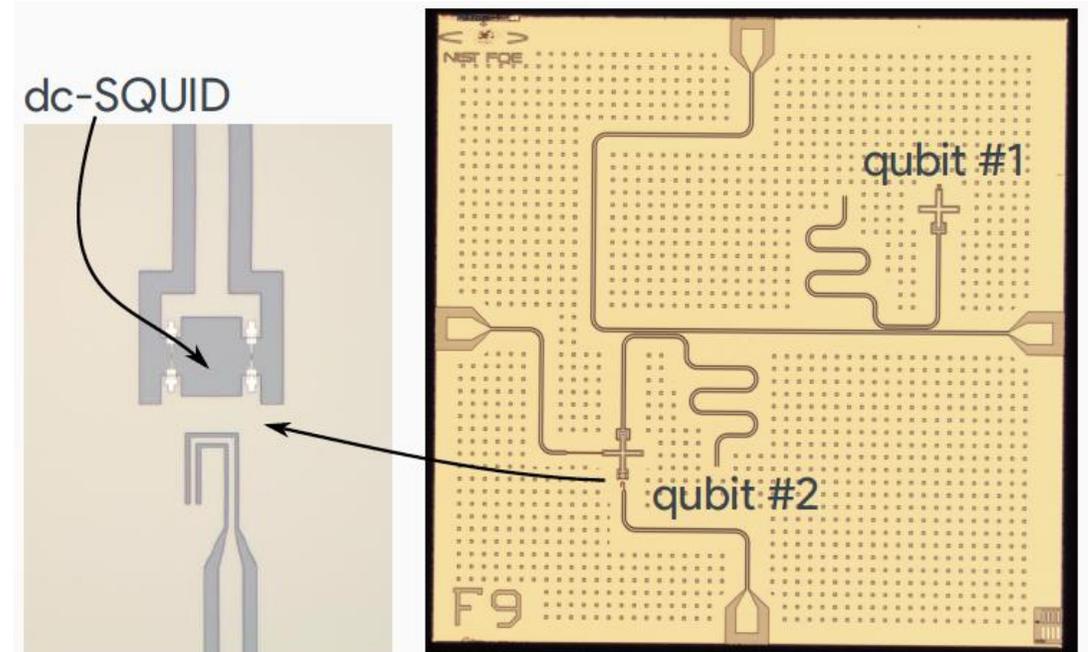


# Achieved in Qubit



**3d Transmon qubit** (TII, Abu Dhabi) in SC 3d cavity (INFN-LNL), measured at INFN-LNF

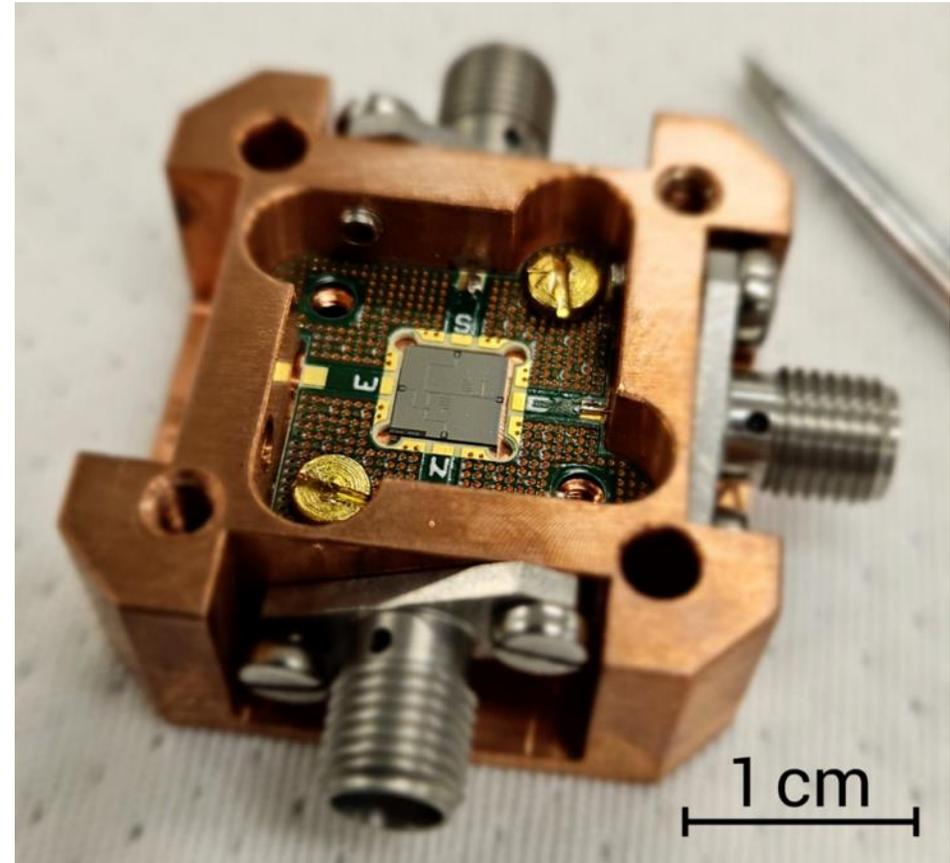
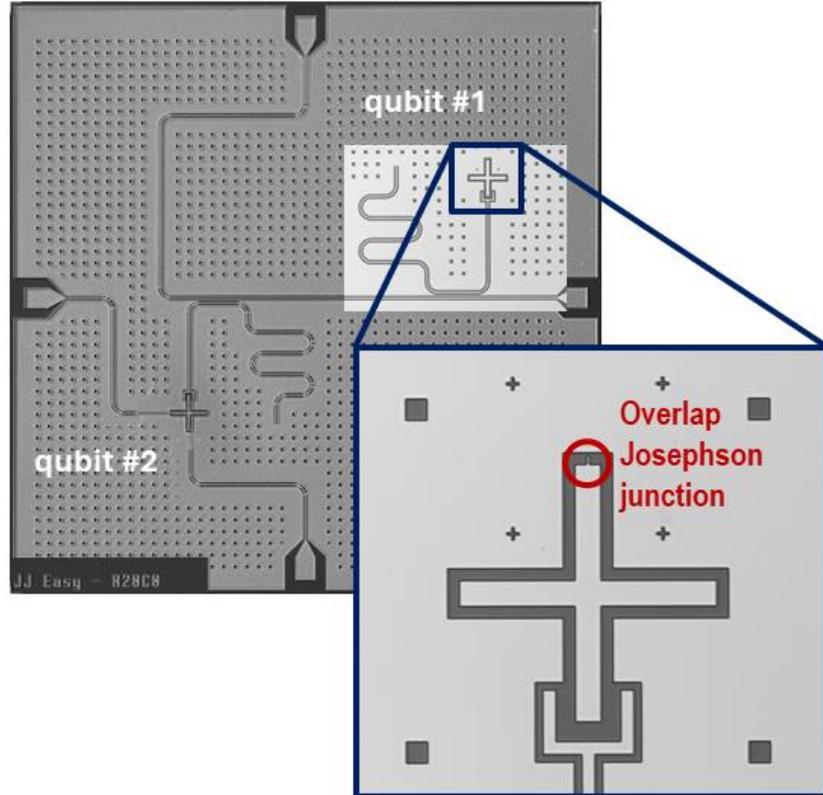
New transmons developed by CNR-INF



**2d Xmon qubit** (NIST) in SC 3d cavity (INFN-LNL), measured at INFN-MIB cyolab.

Flux-bias line to tune the energy spacing between states

# First italian qubit at FBK – 2d Xmon



## 8 INFN Units

- INFN Bologna
- INFN Ferrara
- INFN Firenze
- INFN Lecce
- INFN Milano
- INFN Milano Bicocca
- INFN Gruppo Collegato di Salerno (INFN Napoli)

## 2 INFN National Laboratories

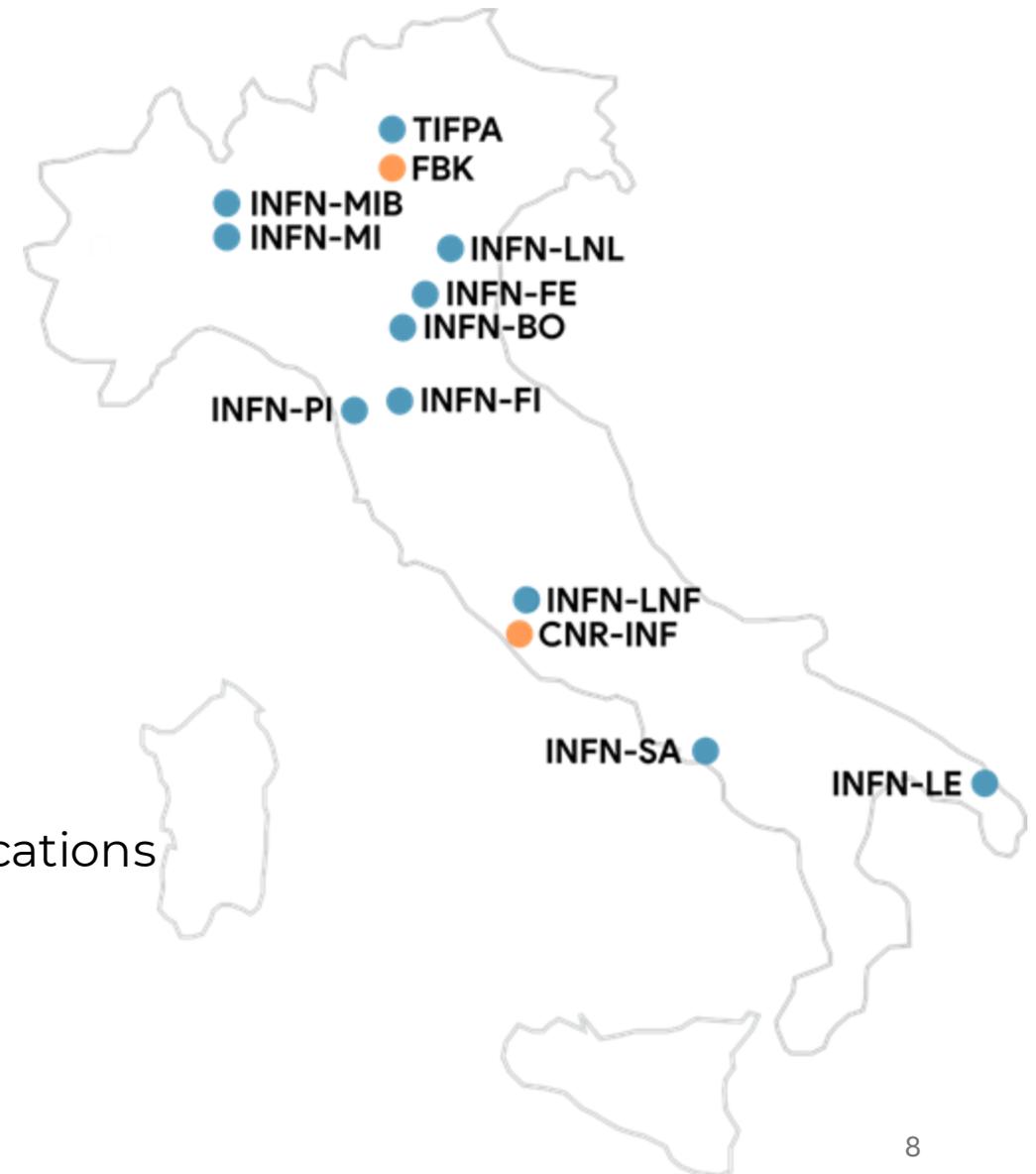
- INFN Laboratori Nazionali di Frascati (LNF)
- INFN Laboratori Nazionali di Legnaro (LNL)

## 1 INFN Research Center

- Trento Institute for Fundamental Physics and Applications (TIFPA).

## 2 External Research Centers

- Fondazione Bruno Kessler (FBK, Trento)
- Istituto di Fotonica e Nanotecnologie (CNR-IFN, Roma)



# Group's size

#	Unit	Number of Researchers	FTE
1	INFN-BO	10	2.2
2	INFN-FE	4	1.1
3	INFN-FI	4	1.4
4	INFN-LE	6	1.2
5	INFN-LNF	11	4.3
6	INFN-LNL	3	1.5
7	INFN-MI	2	1.4
8	INFN-MIB	14	6.4
9	INFN-PI	16	2.55
10	INFN-SA	7	2.2
11	INFN-TIFPA	14	4.4
	<b>Total</b>	<b>91</b>	<b>28.65</b>

# Budget – 3 year's plan

Unit	1st Y [k€]	2nd Y[k€]	3rd Y [k€]	Total [k€]
INFN-BO	20	20.5	14.5	<b>56</b>
INFN-FE	3	3	3	<b>9</b>
INFN-FI	9	4	4	<b>17</b>
INFN-LE	20	19	14	<b>63</b>
INFN-LNF	46	45	45	<b>136</b>
INFN-LNL	13	9	6	<b>28</b>
INFN-MI	15	6	1	<b>15</b>
INFN-MIB	36	23	11	<b>70</b>
INFN-PISA	28	27	21	<b>76</b>
INFN-SA	25	24	22	<b>71</b>
INFN-TIFPA	35	35	35	<b>105</b>
<b>Totale</b>	<b>250</b>	<b>215.5</b>	<b>176.5</b>	<b>642</b>

Chip production (FBK)  
25 k€ / year

Chip production (CNR-IFN)  
20 k€ / year

Cavity production (INFN-LNL)  
5 k€ / year

# Working Packages

Unit	WP1	WP2	WP3	WP4	WP5	WP6	WP7	WP8	WP9
INFN-BO	✓	✓			✓				
INFN-FE					✓				
INFN-FI	✓	✓	✓					✓	
INFN-LE							✓	✓	
INFN-LNF	✓		✓		✓	✓	✓	✓	
INFN-LNL				✓					
INFN-MI	✓				✓				
INFN-MIB		✓			✓	✓	✓		✓
INFN-PI	✓		✓	✓				✓	
INFN-SA		✓				✓	✓		
INFN-TIFPA	✓			✓		✓	✓		
	6	4	3	3	5	4	5	4	1

- **WP1: Theoretical Background** led by *INFN-TIFPA*
- **WP2: Design and simulations of planar (2D) devices** led by *INFN-TIFPA*
- **WP3: Design and simulations of tridimensional (3D) devices** led by *INFN-LNF*
- **WP4: Microfabrication process for superconducting qubits** led by *INFN-PI* and *INFN-TIFPA*
- **WP5: Software and readout system** led by *INFN-MI* and *INFN-MIB*
- **WP6: Quantum Limited Amplifiers** led by *INFN-SA*
- **WP7: Characterization, Measurement and Demonstration** led by *INFN-LNF* and *INFN-MIB*
- **WP8: Application for quantum sensing and Machine Learning** led by *INFN-FI* and *INFN-LNF*
- **WP9: Management and Communication** led by *INFN-MIB*

# Assegnazioni economiche generali

Sez. & Suf.	MISS			CON			ALTRICONS			SEM			TRA			PUB			MAN			INV			LIC-SW			APP			SPSERVIZI			TOTALE				
	Sj	Dot.	Ant.	Sj	Dot.	Ant.	Sj	Dot.	Ant.	Sj	Dot.	Ant.	Sj	Dot.	Ant.	Sj	Dot.	Ant.	Sj	Dot.	Ant.	Sj	Dot.	Ant.	Sj	Dot.	Ant.	Sj	Dot.	Ant.	Sj	Dot.	Ant.					
BO	6.0			5.5																		6.0			2.5							20						
	4.0			4.5																		6.0			2.5							17.0						
FE	3.0																															3						
	3.0																																3.0					
FI	4.0																						5.0										9					
	3.0																						0.0										3.0					
LE	2.0			14.0																			4.0										20					
	2.0			6.0																			0.0										8.0					
LNF	5.0			25.0																		5.0				11.0							46					
	4.0			4.0	20.0																	0.0				9.0							17.0	20.0				
LNL	2.0			11.0																													13					
	2.0			8.0																													10.0					
MI	5.0			10.0																														15				
	2.5			2.0																														4.5				
MIB	6.0							2.0							0.5								25.0			2.5							36					
	4.0							1.0							0.5								0.0	25.0		2.5							8.0	25.0				
PI	4.0			15.5											0.5								6.0			2.0								28				
	4.0			9.0											0.5								0.0			2.0								15.5				
SA	5.5			15.0				2.0																		2.5								25				
	4.0			7.0				2.0																		2.5								15.5				
TIFPA	2.0			33.0																														35				
	0.0			15.5	12.5																													15.5	12.5			
TOTALE	44.5			129				4							1							5			46			9.5		11			250	0				
			44.5				129		4					0			1					0		5		46		9.5		11		0		250				
	32.5		0	0	56	32.5	0	0	3		0	0			1		0	0				0	0	0	6	25	0	0	9.5	0	0	9	0	0	117	57.5	0.0	0.0
			32.5				88.5		3.0				0.0		1.0				0.0			0.0		31.0		9.5		9.0		0.0				174.5				

# Assegnazioni – dettaglio BO

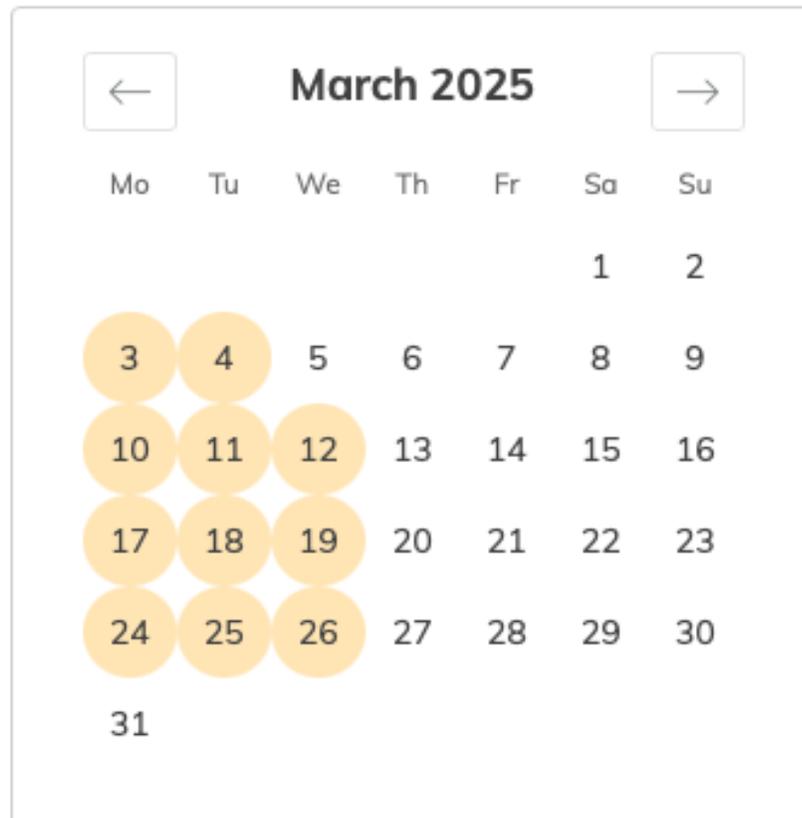
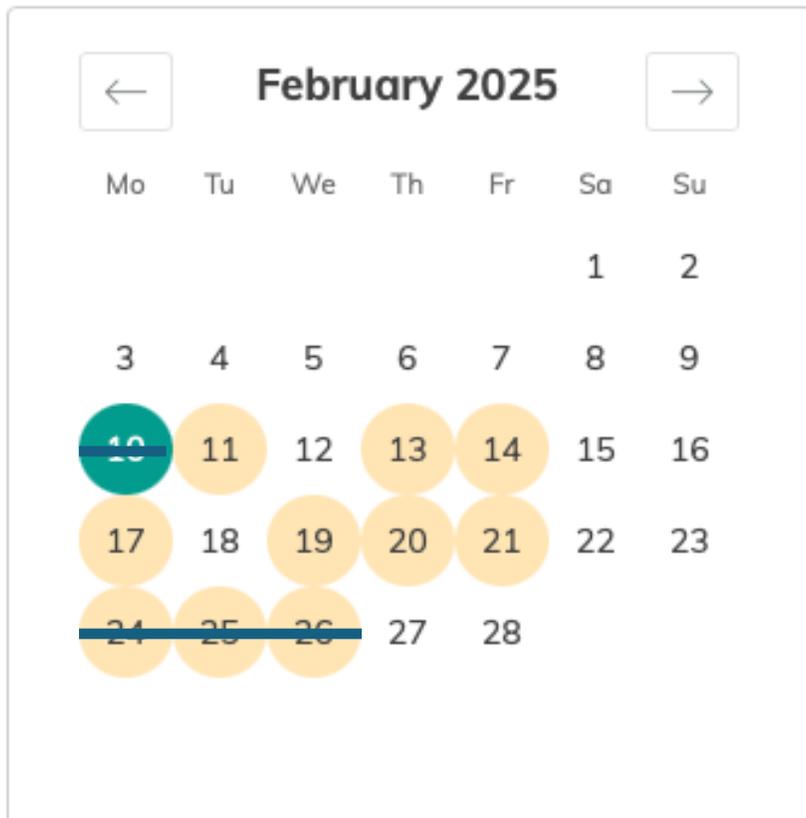
Sigla Loc.	Capitolo	Riunione	Note Alla Richiesta	Rich.	Rich. SJ	Assegn.	Assegn. SJ	Assegn. Dot.	Commento Alla Assegnazione
BO	MISS	Assegnazioni	Missioni presso altri laboratori per sessione di lavoro congiunte e misure. Missioni per lavoro congiunto su scheda zcu208 , software e misure sperimentali; test primo prototipo filtro di Purcell in lettura di >=1 qubit	6.0	0.0	4.0			
		<b>Totale MISS</b>		<b>6.0</b>	<b>0.0</b>	<b>4.0</b>	<b>0.0</b>	<b>0.0</b>	
	CON	Assegnazioni	Consumo generale per materiale RF (connettori, filtri, cavi ecc.)	4.0	0.0	3.0			
		Assegnazioni	2 mixer RF MM1-0212LS , 2 splitter/combiner RF ZX10-2-183-S+ . per up/down conversion analogica	1.5	0.0	1.5			
		<b>Totale CON</b>		<b>5.5</b>	<b>0.0</b>	<b>4.5</b>	<b>0.0</b>	<b>0.0</b>	
	INV	Assegnazioni	Scheda VF-100 (v. allegato) per accedere a tutti i canali ADC/DAC della scheda ZCU111	6.0	0.0	6.0			
		<b>Totale INV</b>		<b>6.0</b>	<b>0.0</b>	<b>6.0</b>	<b>0.0</b>	<b>0.0</b>	
	LIC-SW	Assegnazioni	Contributo CNAF per licenza ANSYS - per progettazione elementi 2d quali un filtro di Purcell.	2.5	0.0	2.5			
		<b>Totale LIC-SW</b>		<b>2.5</b>	<b>0.0</b>	<b>2.5</b>	<b>0.0</b>	<b>0.0</b>	
	<b>Totale BO</b>				<b>20.0</b>	<b>0.0</b>	<b>17.0</b>	<b>0.0</b>	<b>0.0</b>
<b>Totale Generale QUARTET</b>				<b>20.0</b>	<b>0.0</b>	<b>17.0</b>	<b>0.0</b>	<b>0.0</b>	

# Working packages - aggiornati

QUART&T WP leaders	
<b>WP1: Theoretical Background</b>	
Alessandro Roggero (TIFPA)	a.roggero@unitn.it
<b>WP2: Design and simulations of planar devices</b>	
Danilo Labranca (MIB)	danilo.labranca@mib.infn.it
Felix Ahrens (TIFPA)	fahrens@fbk.eu
<b>WP3: Design and simulations of three-dimensional (3D) devices</b>	
Alessandro D'Elia (LNF)	alessandro.delia@Inf.infn.it
Simone Tocci (LNF)	simone.tocci@Inf.infn.it
<b>WP4: Design and simulations of three-dimensional (3D) devices</b>	
Claudio Puglia (PI)	claudio.puglia@pi.infn.it
Federica Mantegazzini (TIFPA)	fmantegazzini@fbk.eu
<b>WP5: Hardware and Software development</b>	
Stefano Carazza (MI)	stefano.carazza@unimi.it
Andrea Giachero (MIB)	andrea.giachero@mib.infn.it
<b>WP6: Quantum Limited Amplifiers</b>	
Sergio Pagano (SA)	spagano@unisa.it
Nicolò Crescini (TIFPA)	ncrescini@fbk.eu
<b>WP7: Characterization, Measurement and Demonstration</b>	
Alessio Rettaroli (LNF)	alessio.rettaroli@Inf.infn.it
Marco Faverzani (LNF)	marco.faverzani@mib.infn.it
<b>WP8: Application for Quantum Sensing and Machine Learning</b>	
Leonardo Banchi (FI)	leonardo.banchi@unifi.it
Claudio Gatti (LNF)	claudio.gatti@Inf.infn.it

External Institutions	
<b>FBK</b>	
Federica Mantegazzini (FBK)	fmantegazzini@fbk.eu
<b>CNR</b>	
Francesco Chiarello (IFN-CNR)	francesco.mattioli@cnr.it

# Date kick-off



**h 9-13, 14-18**

il 10/2

**h 8-12, 14-18**

# Info ANSYS

- Piattaforma disponibile
- Istruzioni (datate): <https://web.pd.infn.it/CCR/6-ansys-enab>
- Bisogna registrarsi poi indirizzare il license server [lm-ansys.infn.it](http://lm-ansys.infn.it)
  - Si usano sempre le porte standard dei vari licence manager, per cui è sufficiente istruire l'installazione con il solo nome del server
- Ansys CFD, EM ed HFSS
- Anche licenze di Granta, Lumerical e Zemax
- Da Ingegneria serve una VPN INFN
  - Il controllo viene fatto anche sullo user id di chi si registra (un utente non registrato non può accedere al software)

# Attività BO

- Manipolazione/readout tramite Xilinx/AMD ZCU111 (gen.1) + ZCU208? (gen.3)
  - Matteo Franchini
- Filtro di Purcell
  - Simona Zaccaria
- Sarà possibile anche partecipare a WP diversi da quelli in cui formalmente ci si trova
- Definire un giorno/ora che vada bene a tutti per briefing regolari (al momento opportuno)

The Nanofabrication facility is located in a 500 square meters, 100-1000 class (ISO5 – ISO6) clean room, in the Rome ARToV (Area della Ricerca di Tor Vergata) Research Area.



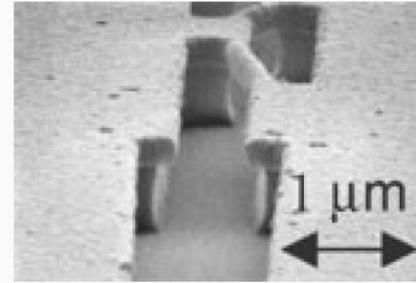
## Voyager Raith Electron Beam Lithography system

Resolution up to 10 nm, sample sizes up to 6", realignment on markers



## Balzers 510 evaporation system

Load lock for on site oxidation, tilted angle evaporation



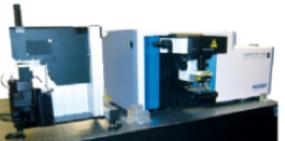
## SEM image of a suspended bilayer bridge

for the fabrication of Al/AlO<sub>x</sub>/Al junctions using double angle shadow evaporation

### Main Tools:

- E-Beam microfabricator
- Mask aligner
- Sputtering
- Evaporator (tilted angle)
- RIE (Reactive Ion Etching)
- ICP (Inductively Coupled Plasma)
- SEM (Scanning Electron Microscope)
- AFM (Atomic Force Microscope)
- Optical microscopes
- Ultrasonic bonder
- Profilometer
- Scriber
- Resist spinner
- Ovens
- Chemicals

**Successfully produced Josephson junctions** for the INFN Project Qub-IT and SIMP;



- **CR-D:** 700 m<sup>2</sup>, Class 10/100, 0.8 μm CMOS pilot line: Ion Implantation, Oxidation, Diffusion, RIE, Deep RIE (silicon and oxide), Lithography (0.35 μm + mask aligner + EBL), metal sputtering, optical profilometry;
- **CR-M:** 500 m<sup>2</sup>, Class 100/1000, diffusion, lithography (mask aligner + laser writer), wafer bonding, electroplating, Si bulk micromachining, metal evaporation, rf magnetron sputtering, RIE, mechanical and optical profilometry;
- **CR-3D:** m<sup>2</sup>, Class 10/100, CMP, thinning, bonding, ALD, metrology;
- **Testing Area:** 300 m<sup>2</sup>; manual parametric testing, automatic parametric/functional testing, optical testing (spectral responsivity, quantum efficiency), solar cells efficiency characterization, gas and pressure sensors test benches;
- **Integration Area:** 100 m<sup>2</sup>, Class 1000 Microassembly station; screen printing, bonding (ball & wedge bonder), Shear-Pull, Tester, reflow oven, CNC micro-mill, pick and place
- **Nano- and Micro- Analytical Facility:** Nano Ramen, FIB-SEM-EDX-EBSD, D-SIMS, TOF-SIMS, XPS, AFS, XRD/XRF;

**Successfully produced Josephson junction** for the JPAs and qubits within the NQSTI and Qub-IT project;